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Team Nexperia

PEMB13; PUMB13

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

Rev. 4 — 7 December 2011

Product data sheet

1. Product profile

1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			NPN/NPN	Package	
	NXP	JEITA	complement	complement	configuration	
PEMB13	SOT666	-	PEMD13	PEMH13	ultra small and flat lead	
PUMB13	SOT363	SC-88	PUMD13	PUMH13	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Parameter	Conditions	Min	Тур	Max	Unit
tor					
collector-emitter voltage	open base	-	-	-50	V
output current		-	-	-100	mA
bias resistor 1 (input)		3.3	4.7	6.1	kΩ
bias resistor ratio		8	10	12	
	collector-emitter voltage output current bias resistor 1 (input)	collector-emitter voltage open base output current bias resistor 1 (input)	collector-emitter voltage open base - output current - bias resistor 1 (input) 3.3	collector-emitter voltage open base output current bias resistor 1 (input) 3.3 4.7	tor collector-emitter voltage open base50 output current100 bias resistor 1 (input) 3.3 4.7 6.1



2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			1 2 3
			006aaa212

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMB13	-	plastic surface-mounted package; 6 leads	SOT666
PUMB13	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMB13	45
PUMB13	B*5

[1] * = placeholder for manufacturing site code

5. Limiting values

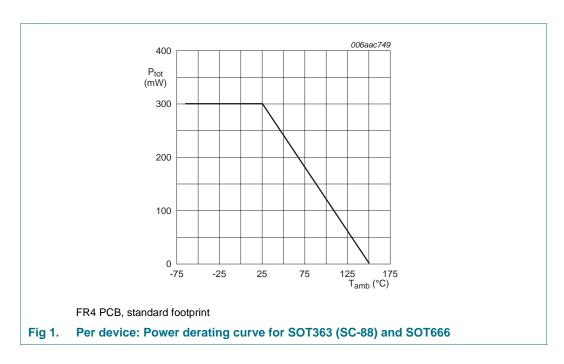
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	- 5	V
V_{I}	input voltage				
	positive		-	+5	V
	negative		-	-30	V
Io	output current		-	-100	mA
I _{CM}	peak collector current	$\begin{array}{l} \text{single pulse;} \\ t_p \leq 1 \text{ ms} \end{array}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PEMB13 (SOT666)		[1][2] _	200	mW
	PUMB13 (SOT363)		<u>[1]</u> -	200	mW
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PEMB13 (SOT666)		[1][2] _	300	mW
	PUMB13 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

 $[\]begin{tabular}{ll} [2] & Reflow soldering is the only recommended soldering method. \end{tabular}$



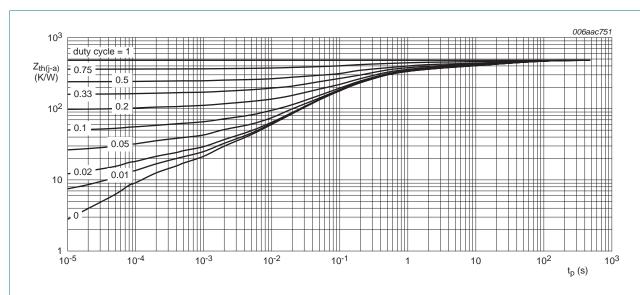
6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air				
	PEMB13 (SOT666)		[1][2]	-	625	K/W
	PUMB13 (SOT363)		<u>[1]</u> _	-	625	K/W
Per device	9					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMB13 (SOT666)		[1][2]	-	417	K/W
	PUMB13 (SOT363)		<u>[1]</u> -	-	417	K/W

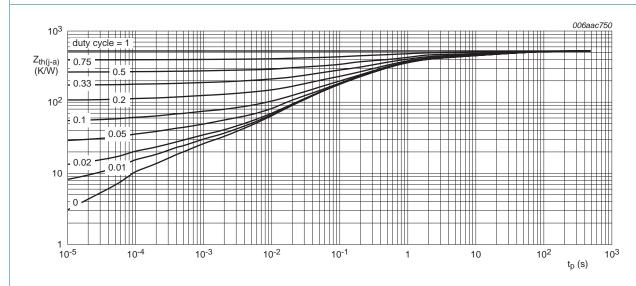
^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMB13 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMB13 (SOT363); typical values

PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

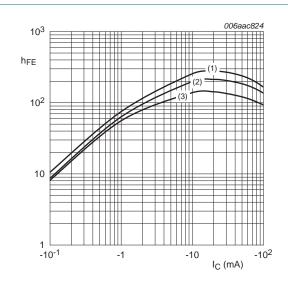
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I_{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μΑ
	current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	- 5	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-170	μА
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	-	-	-100	mV
$V_{I(off)}$	off-state input voltage	V_{CE} = -5 V; I_{C} = -100 μA	-	-0.6	-0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -5 \text{ mA}$	-1.3	-0.9	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	$k\Omega$
R2/R1	bias resistor ratio		8	10	12	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ [1] $f = 100 \text{ MHz}$	-	180	-	MHz

^[1] Characteristics of built-in transistor



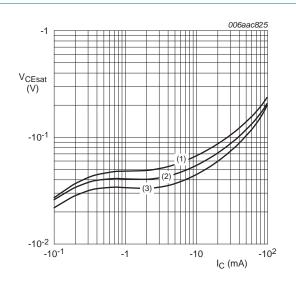
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 4. DC current gain as a function of collector current; typical values



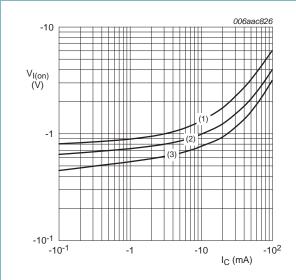
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



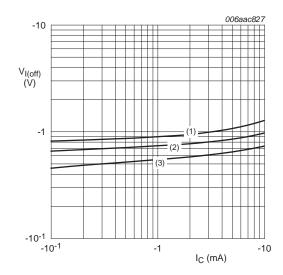


(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) T_{amb} = 100 °C

Fig 6. On-state input voltage as a function of collector current; typical values



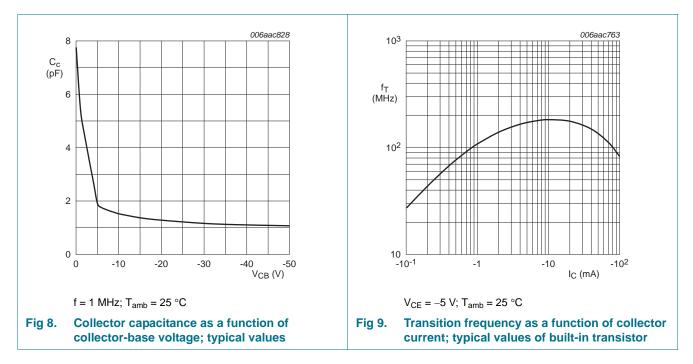
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. Off-state input voltage as a function of collector current; typical values

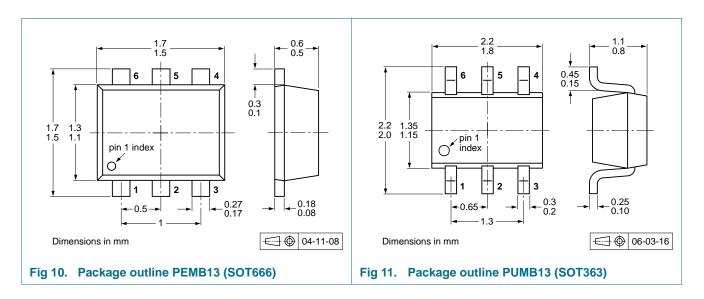


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



PEMB13_PUMB13

10. Packing information

 Table 9.
 Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

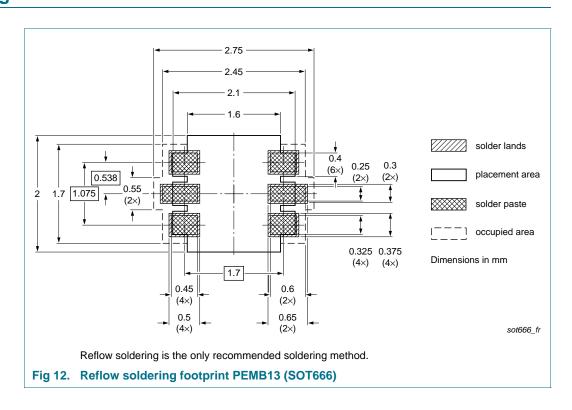
Туре	Package	Description		Packing quantity				
number			3000	4000	8000	10000		
PEMB13	PEMB13 SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-		
		4 mm pitch, 8 mm tape and reel	-	-115	-	-		
PUMB13	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-	-	-135		
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165		

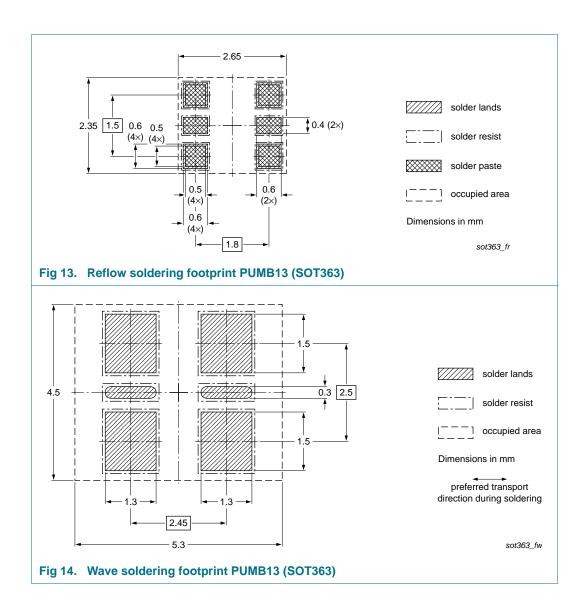
[1] For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

[3] T2: reverse taping

11. Soldering





PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

12. Revision history

Table 10. Revision history

1B13 v.3						
ity						
 Legal texts have been adapted to the new company name where appropriate. 						
Section 1 "Product profile": updated						
Section 4 "Marking": updated						
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ıs						
1B13 v.2						
;						

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMB13_PUMB13

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PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

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NSBC114YF3T5G NSBC123TF3T5G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F)

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SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G

DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G